

DESCRIPTION

The SD1146 is a 12.5 V Class C epitaxial silicon NPN planar transistor designed primarily for UHF communications. This device utilizes improved metallization to achieve infinite VSWR at rated operating conditions.

IMPORTANT: For the most current data, consult MICROSEMI's website: <http://www.microsemi.com>

KEY FEATURES

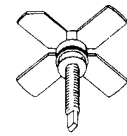
470 MHz
12.5 Volts
Efficiency 60%
Common Emitter
 $P_{OUT} = 10 \text{ W Min.}$
 $G_P = 6.0 \text{ dB Gain}$

APPLICATIONS/BENEFITS

UHF Mobile
Applications

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^\circ\text{C}$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	36	V
V_{CEO}	Collector-Emitter Voltage	16	V
V_{CES}	Collector-Emitter Voltage	36	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Device Current	2.0	A
P_{DISS}	Power Dissipation	37.5	W
T_J	Junction Temperature	+200	$^\circ\text{C}$
T_{STG}	Storage Temperature	-65 to +150	$^\circ\text{C}$

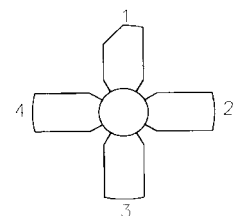


.280 4L STUD (M122)
epoxy sealed

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	4.7	$^\circ\text{C/W}$
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PIN CONNECTION



1. Collector 3. Base
2. Emitter 4. Emitter

Note : Above parameters , ratings , limits and conditions are subject to change.

▶ **STATIC ELECTRICAL SPECIFICATIONS (T_{CASE} = 25 °C)**

Symbol	Test Conditions	SD1146			Units
		Min.	Typ.	Max.	
BV_{CES}	I_C = 200 mA V_{BE} = 0 V	36	—	—	V
BV_{CEO}	I_C = 200 mA	16	—	—	V
BV_{EBO}	I_E = 4 mA I_C = 0 mA	4.0	—	—	V
I_{CBO}	V_{CB} = 15 V I_E = 0 mA	—	—	2	mA
I_{CES}	V_{CE} = 15 V I_C = 0 mA	—	—	5	mA
h_{FE}	V_{CE} = 5 V I_C = .5 A	20	—	200	—

▶ **DYMANIC ELECTRICAL SPECIFICATIONS (T_{CASE} = 25 °C)**

Symbol	Test Conditions	SD1146			Units
		Min.	Typ.	Max.	
P_{OUT}	f = 470 MHz P_{IN} = 2.5 W V_{CE} = 12.5 V	10	—	—	W
η_C	f = 470 MHz P_{IN} = 2.5 W V_{CE} = 12.5 V	60	—	—	%
G_P	f = 470 MHz P_{IN} = 2.5 W V_{CE} = 12.5 V	6	—	—	dB
C_{OB}	f = 1 MHz V_{CB} = 12.5 V	—	—	45	pF

▶ **IMPEDANCE DATA**

Freq.	Z _{IN} (Ω)	Z _{CL} (Ω)
470 MHz	1.6 + j 2.2	6.0 - j 0.34

P_{OUT} = 10.0 W

V_{CC} = 12.5 V

Note : Above parameters , ratings , limits and conditions are subject to change .